

Synthesis and Characterization of Nanoporous TiO, Films on Silicon Substrates for Solar Cells Applications

E. Manea, A. Popescu, C. Podaru, M. Purica, F. Comanescu, V. Schiopu, M. Danila, C. Parvulescu, E. Budianu

National Institute for Research and Development in Microtechnology, Str. Erou lancu Nicolae 126A, Bucharest, Romania

e-mail: elena.manea@imt.ro

Experimental

Titanium oxide is an interesting and versatile material which is used in many areas of technology, including high efficiency, low cost solar-cells applications due to its chemical inertness, ecofriendly nature and photostability.

Depending on fabricating conditions and further heat treatment titanium oxide can be obtain in several polymorphic forms, including anatase and rutile.

In this work nanoporous titania was investigated in order to achieve a n-TiO₂/Si heterojunction by anodization process which is compatible with silicon photovoltaic technology.



TiO₂ samples for solar cells applications were prepared by the electrochemical oxidation of pure titanium thin film deposited onto various substrate types including silicon, SiO₂ and borosilicate glass. Titanium layers of 100 nm thickness were deposited on substrate by sputtering.

Anodization was conducted using a conventional two – electrode system. The influence of anodizing parameters on the surface morphology was investigated in detail to optimize the process in order to obtain the porous structure. The best results have been obtained using a mixture of NH₄F in ethylene - glycol as electrolyte. The applied voltage is 5 V, anodisation time, 120 s, T=300K. The distance between the working and counter - electrode was kept at 5 cm. After anodization, samples were washed, dried and treated at different temperature from 400 to 800 °C.

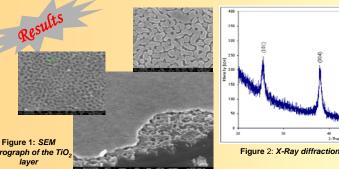
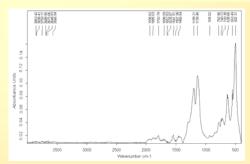
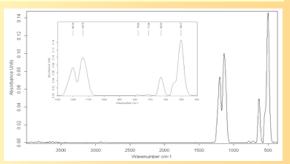


Figure 2: X-Ray diffraction pattern of a TiO2 layer





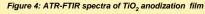


Figure 5: ATR-FTIR spectra of TiO, annealing film

Nanostructured titanium oxide films for photovoltaic applications have been obtained by anodization of titanium thin films deposited by sputtering.

The dependence of layers morphology on anodizing parameters was evaluated in order to optimize the process.

Figure 3: Raman spectra of TiO2 layers on silicon substrates obtained by anodization process